Korean International Semiconductor Conference & Exhibition
on Manufacturing Technology 2025

KISM 2025 BUSAN

Re:Innovation of Semiconductor Manufacturing for AI Ecosystem

[TuD2] Power Devices II	
Session Date	November 11 (Tue.), 2025
Session Time	14:50-16:30
Session Room	Room D (Sydney Room, 2F)
Session Chair	Prof. Ho-Jun Lee (Pusan Nat'l Univ., Korea)

[TuD2-1] [Invited] **14:50-15:15**

Radiation-Hardened Edge Termination Design for SiC Power Devices under Proton

Ogyun Seok (Pusan Nat'l Univ., Korea)

[TuD2-2] [Invited] **15:15-15:40**

Development Status of SiC MOSFET in Powermaster Semiconductor

Hongki Kim and Jaegil Lee (Powermaster Semiconductor, Korea)

[TuD2-3] [Invited] **15:40-16:05**

Fabrication of SiC SBD for 6.5 kV Edge-Termination Designs

Sung Mo Koo, Weon Chan Kim, Dong Ju Kang (EYEQ Lab Inc., Korea), Jun Seong Kim, Hyemin Kang (KENTECH, Korea), Sang Gi Kim, and Gwon Je Kim (EYEQ Lab Inc., Korea)

[TuD2-4] [Invited] **16:05-16:30**

Performance of TES Tunable SiC Epitaxial System “TRION”

Geumchan Hwang and Ray Suh (TES, Korea)